MOSFETs Silicon N-Channel MOS

# SSM6N56FE

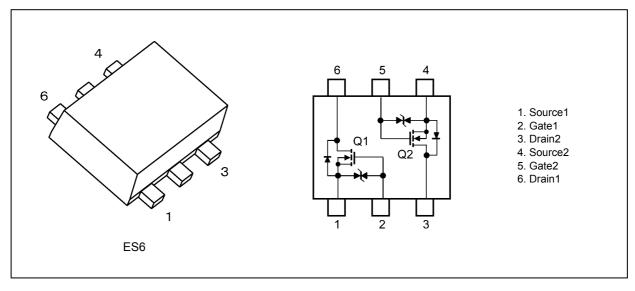
### 1. Applications

High-Speed Switching

#### 2. Features

- (1) 1.5-V gate drive voltage.
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 235 \text{ m}\Omega \text{ (max)}$  (@V<sub>GS</sub> = 4.5 V, I<sub>D</sub> = 800 mA)
  - $R_{DS(ON)}$  = 300 m $\Omega$  (max) (@V\_{GS} = 2.5 V,  $I_{D}$  = 600 mA)
  - $R_{DS(ON)}$  = 480 m $\Omega$  (max) (@V\_{GS} = 1.8 V,  $I_D$  = 200 mA)
  - $\mathrm{R}_{\mathrm{DS(ON)}}$  = 840 m $\Omega$  (max) (@V\_{\mathrm{GS}} = 1.5 V,  $\mathrm{I}_{\mathrm{D}}$  = 50 mA)

#### 3. Packaging and Pin Assignment



### Absolute Maximum Ratings (Note) (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	20	V
Gate-source voltage		V <sub>GSS</sub>	±8	
Drain current (DC)	(Note 1)	I <sub>D</sub>	800	mA
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	1600	]
Power dissipation	(Note 2)	PD	150	mW
Power dissipation	(Note 3)		250	1
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Device mounted on an FR-4 board.(total dissipation)

- Note 3: Device mounted on an FR-4 board.(total dissipation) (25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm ,Cu pad: 645 mm<sup>2</sup>)
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

<sup>(25.4</sup> mm × 25.4 mm × 1.6 mm ,Cu pad: 0.135 mm<sup>2</sup> × 6)

#### 5. Electrical Characteristics

#### 5.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)(Q1,Q2 Common)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±6 V	_	_	±1	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V	_		1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	20	—	—	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = -5 V	15	_	_	
Gate threshold voltage	(Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 1 mA	0.4	—	1.0	
Drain-source on-resistance	(Note 3)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 50 mA, V <sub>GS</sub> = 1.5 V	—	360	840	mΩ
			I <sub>D</sub> = 200 mA, V <sub>GS</sub> = 1.8 V	_	290	480	
			I <sub>D</sub> = 600 mA, V <sub>GS</sub> = 2.5 V	_	230	300	
			I <sub>D</sub> = 800 mA, V <sub>GS</sub> = 4.5 V	_	186	235	
Forward transfer admittance	(Note 3)	Y <sub>fs</sub>	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 200 mA	_	1.4	—	S

Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 3: Pulse measurement.

#### 5.2. Dynamic Characteristics (Unless otherwise specified, Ta = 25 °C)(Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,	_	55	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	6	_	
Output capacitance	C <sub>oss</sub>		_	16	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA,	_	5.5	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$V_{GS}$ = 0 to 2.5 V, $R_{G}$ = 50 $\Omega$	_	8.5	_	

### 5.3. Switching Time Test Circuit

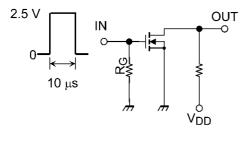


Fig. 5.3.1 Switching Time Test Circuit

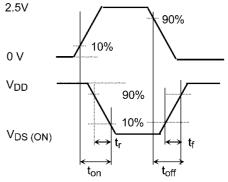


Fig. 5.3.2 Input Waveform/Output Waveform

### 5.4. Gate Charge Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 800 mA,	_	1.0	_	nC
Gate-source charge 1	Q <sub>gs1</sub>	V <sub>GS</sub> = 4.5 V	_	0.12	_	
Gate-drain charge	Q <sub>gd</sub>		_	0.4	_	

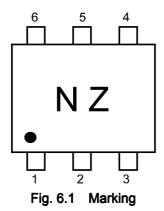
Note 2: Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current (I<sub>D</sub>) to below (1 mA for this device). Then, for normal switching operation,  $V_{GS(ON)}$  must be higher than  $V_{th}$ , and  $V_{GS(OFF)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$ . Take this into consideration when using the device.

## 5.5. Source-Drain Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C) (Q1,Q2 Common)

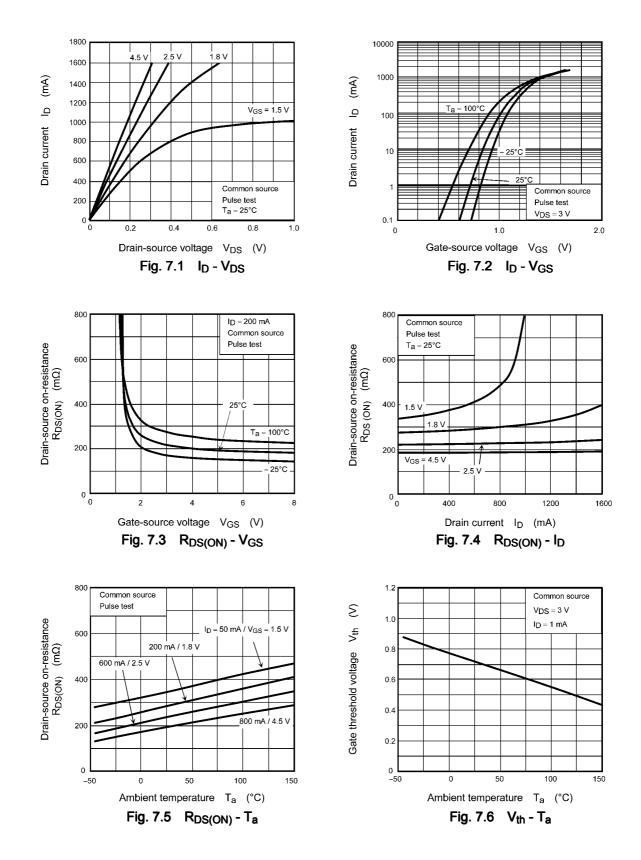
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{\text{DSF}}$	$I_{\rm D}$ = -0.8 A, $V_{\rm GS}$ = 0 V	_	-0.82	-1.2	V

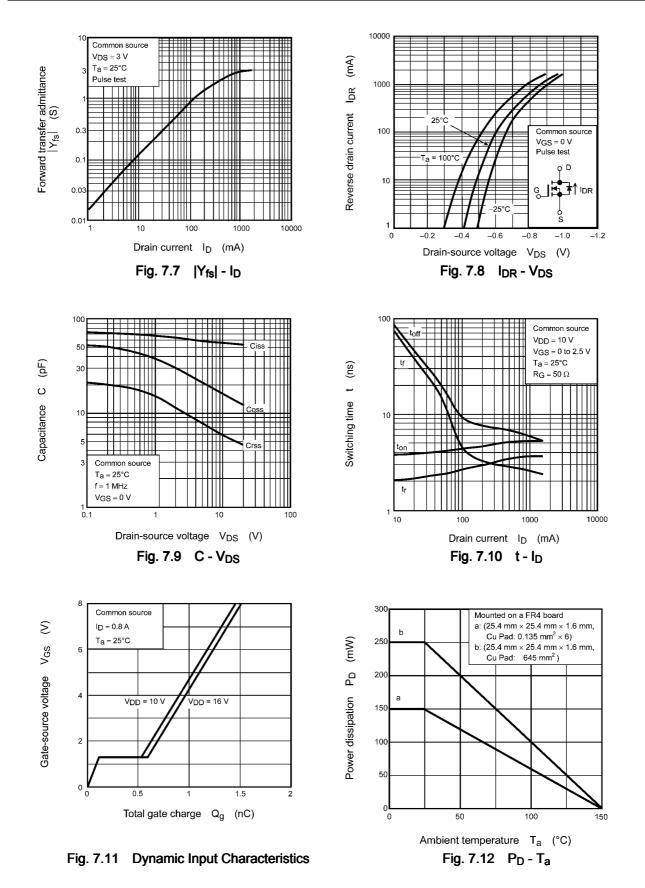
Note 1: Pulse measurement.

### 6. Marking



### 7. Characteristics Curves (Q1,Q2 Common) (Note)





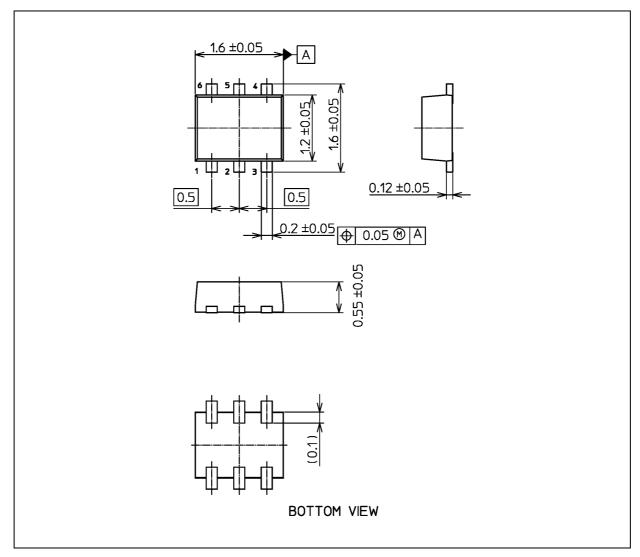
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### SSM6N56FE

### Package Dimensions

Unit: mm



Weight: 3.0 mg (typ.)

Package Name(s) Nickname: ES6

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